

N-channel LFPAK 80 V 11 mΩ standard level MOSFET

Rev. 02 — 28 October 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

Improved mechanical and thermal characteristics LEBAK provides maximum power

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	67	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	18	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ T _j = 25 °C; see Figure 12;	-	8.6	11	mΩ

see Figure 13



N-channel LFPAK 80 V 11 mΩ standard level MOSFET

Table 1.	Quick reference datac	ontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A};$	-	11	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	45	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 67 \text{ A}; \ V_{sup} \leq 80 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ unclamped \end{array} $	-	-	121	mJ

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3.	Ordering information			
Type num	ber	Package		
		Name	Description	Version
PSMN011-	80YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$ \begin{array}{cccccccccccccccccccccccccccccccccccc$						
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
$\begin{split} & \text{l}_{D} & \text{drain current} & \begin{matrix} V_{GS} = 10 \text{ V}; \text{ $T_{mb} = 100 \ ^{\circ}C$; see Figure 1} & - & 47 \\ \hline & V_{GS} = 10 \text{ V}; \text{ $T_{mb} = 25 \ ^{\circ}C$; see Figure 1} & - & 67 \\ \hline & V_{GS} = 10 \text{ V}; \text{ $T_{mb} = 25 \ ^{\circ}C$; see Figure 3} & - & 266 \\ \hline & P_{tot} & \text{total power dissipation} & T_{mb} = 25 \ ^{\circ}C$; see Figure 2} & - & 117 \\ \hline & T_{stg} & \text{storage temperature} & -55 & 175 \\ \hline & T_{stg} & \text{storage temperature} & -55 & 175 \\ \hline & T_{std(M)} & \text{peak soldering temperature} & - & 260 \\ \hline & \textbf{Source-drain diode} & & & & & \\ \hline & I_{S} & \text{source current} & T_{mb} = 25 \ ^{\circ}C & - & 266 \\ \hline & I_{SM} & \text{peak source current} & \text{pulsed}; \text{ $t_p \leq 10 \ \mu\text{s}; \text{ $T_{mb} = 25 \ ^{\circ}C} & - & 266 \\ \hline & \textbf{Avalanche ruggedness} & & & & \\ \hline & E_{DS(AL)S} & \text{non-repetitive drain-source} & V_{GS} = 10 \text{ V}; \text{ $T_{j(init)} = 25 \ ^{\circ}C$; I_{D} = 67 \text{ A;} & - & 121 \\ \end{split}$	V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
VGS = 10 V; Tmb = 25 °C; see Figure 1-67IDMpeak drain currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$; see Figure 3-266Ptottotal power dissipation $T_{mb} = 25 \ ^{\circ}C$; see Figure 2-117Tstgstorage temperature-55175Tjjunction temperature-55175Tsld(M)peak soldering temperature-260Source-drain diodeIssource current $T_{mb} = 25 \ ^{\circ}C$ -67Ispeak source current $T_{mb} = 25 \ ^{\circ}C$ -67Issource current $T_{mb} = 25 \ ^{\circ}C$ -67Isnon-repetitive drain-source $V_{GS} = 10 \ V; T_{j(init)} = 25 \ ^{\circ}C; \ I_D = 67 \ A;$ -121	V _{GS}	gate-source voltage		-20	20	V
$\begin{split} & \text{los} \text{triang} t$	I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	47	А
P_{tot} total power dissipation $T_{mb} = 25 \ ^{\circ}C$; see Figure 2-117 T_{stg} storage temperature-55175 T_j junction temperature-55175 $T_{sld(M)}$ peak soldering temperature-260Source-drain diodeI I_S source current $T_{mb} = 25 \ ^{\circ}C$ -67 I_{SM} peak source currentpulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$ -266Avalanche ruggedness $E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \ V$; $T_{j(init)} = 25 \ ^{\circ}C$; $I_D = 67 \ A$;-121			V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	67	А
T_{stg} storage temperature-55175 T_j junction temperature-55175 $T_{sld(M)}$ peak soldering temperature-260Source-drain diodeIssource current $T_{mb} = 25 \text{ °C}$ -67IsMpeak source currentpulsed; $t_p \le 10 \ \mu\text{s}; T_{mb} = 25 \text{ °C}$ -266Avalanche ruggednessVGS = 10 V; $T_{j(init)} = 25 \text{ °C}; I_D = 67 \ A;$ -121	I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	266	А
Tjjunction temperature-55175T_{sld(M)}peak soldering temperature-260Source-drain diodeIssource current $T_{mb} = 25 \ ^{\circ}C$ -67IsMpeak source currentpulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$ -266Avalanche ruggednessVGS = 10 V; $T_{j(init)} = 25 \ ^{\circ}C$; $I_D = 67 \ A$;-121	P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	117	W
$\begin{array}{c c} T_{sld(M)} & \text{peak soldering temperature} & - & 260 \\ \hline \textbf{Source-drain diode} & & & & \\ I_S & \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 67 \\ \hline I_{SM} & \text{peak source current} & \text{pulsed; } t_p \leq 10 \ \mu\text{s; } T_{mb} = 25 \ ^{\circ}\text{C} & - & 266 \\ \hline \textbf{Avalanche ruggedness} & & & \\ \hline \textbf{E}_{DS(AL)S} & \text{non-repetitive drain-source} & V_{GS} = 10 \ \text{V; } T_{j(init)} = 25 \ ^{\circ}\text{C; } I_D = 67 \ \text{A;} & - & 121 \\ \hline \end{array}$	T _{stg}	storage temperature		-55	175	°C
Source-drain diodeIssource current $T_{mb} = 25 \text{ °C}$ -67I_{SM}peak source currentpulsed; $t_p \le 10 \mu\text{s}; T_{mb} = 25 \text{ °C}$ -266Avalanche ruggednessEEEEEDS(AL)Snon-repetitive drain-sourceVGS = 10 V; T_j(init) = 25 °C; ID = 67 A;-121	Tj	junction temperature		-55	175	°C
Issource current $T_{mb} = 25 \ ^{\circ}C$ -67IsMpeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -266Avalanche ruggednessVGS = 10 V; $T_{j(init)} = 25 \ ^{\circ}C; I_D = 67 \ A;$ -121	T _{sld(M)}	peak soldering temperature		-	260	°C
$\label{eq:source} \begin{array}{ccc} \mbox{peak source current} & \mbox{pulsed; } t_p \leq 10 \ \mbox{\mus; } T_{mb} = 25 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	Source-drain	n diode				
Avalanche ruggedness $E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 67 \text{ A};$ -121	I _S	source current	T _{mb} = 25 °C	-	67	А
$E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 67 \text{ A};$ - 121	I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	266	А
	Avalanche r	uggedness				
	$E_{DS(AL)S}$	•	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 67 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω ; unclamped	-	121	mJ

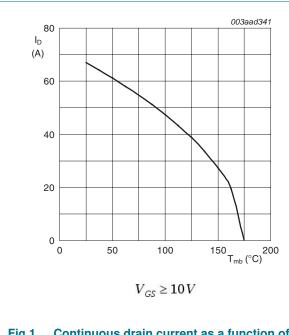
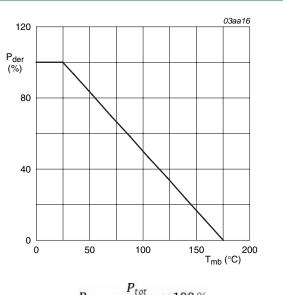


Fig 1. Continuous drain current as a function of mounting base temperature

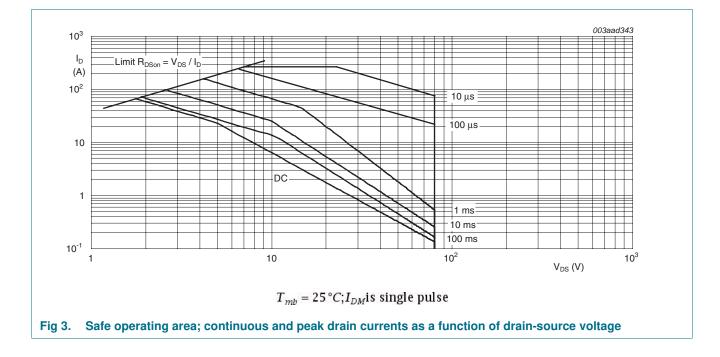


$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



PSMN011-80YS
Product data sheet

PSMN011-80YS



Thermal characteristics 5.

0.05 0.02

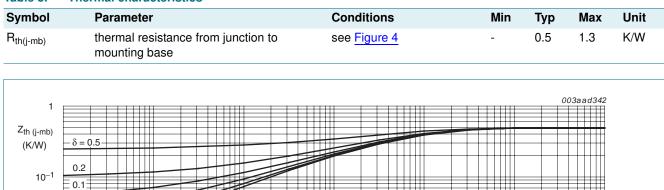
single shot

10-2

10⁻³

Fig 4.

1-6



10^{_3}

10-2

10-1

1

tp (s)

Table 5. **Thermal characteristics**

Transient thermal impedance from junction to mounting base as a function of pulse duration; typical
values

10-4

10⁻⁵

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	73	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V	
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I _{GSS}	s gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	-	19	26	mΩ
	V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	18	mΩ	
	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	8.6	11	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	38	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	45	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	13	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u>	-	8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{see } \frac{\text{Figure } 15}{\text{see } \frac{1}{12}}$	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2800	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	270	-	pF
C _{rss}	reverse transfer capacitance		-	146	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 1.6 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	23	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	20	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	12	-	ns

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Symbol

Source-drain diode

PSMN011-80YS

Тур

Unit

Max

N-channel LFPAK 80 V 11 mΩ standard level MOSFET

Min

V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 2$ see <u>Figure 17</u>	5 °C; -	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 40 A; dI _S /dt = 100 A/με	s; -	54	-	ns
Qr	recovered charge	V_{GS} = 0 V; V_{DS} = 40 V	-	98	-	nC
100 I _D (A) 80		03aad311 100 5.5- (A) 80			003aad333	
60		60				
40		40				
20	V _{GS} (V	20	Tj = 1	75 °C	-T _j = 25 °C -	
	0 1 2	/ _{DS} (V) ³ 0	2	4	6 V _{GS} (V)	
Fig 5. ($T_j = 25 ^{\circ}C$ Output characteristics: drain cu	rrent as a Fig 6. Trar	$V_{DS} > I_D$ nsfer characteris		n current a	as a
	unction of drain-source voltage		tion of gate-sou			
100	0	03aad338 4000			003aad337	
g _{fs}		C			C _{iss}	
(S) 80		3500				
00						
		3000				
60		3000				
60						
60 40		2500				
					C _{rss}	
		2500			C _{rss}	
40		2500				
40 20 0		2500 2000 1500 1000	5 10	15		
40 20 0	$T_{j} = 25 °C; V_{DS} = 25V$	2500 2000 1500	$V_{DS} = 0V; J$		20 _{VGS} (V) ²⁵	

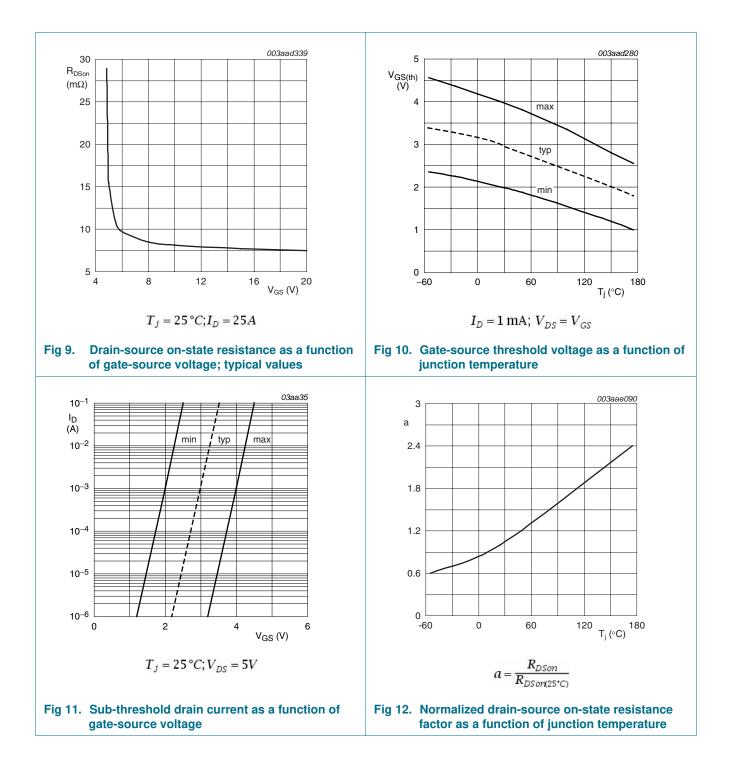
Conditions

Table 6. Characteristics ...continued

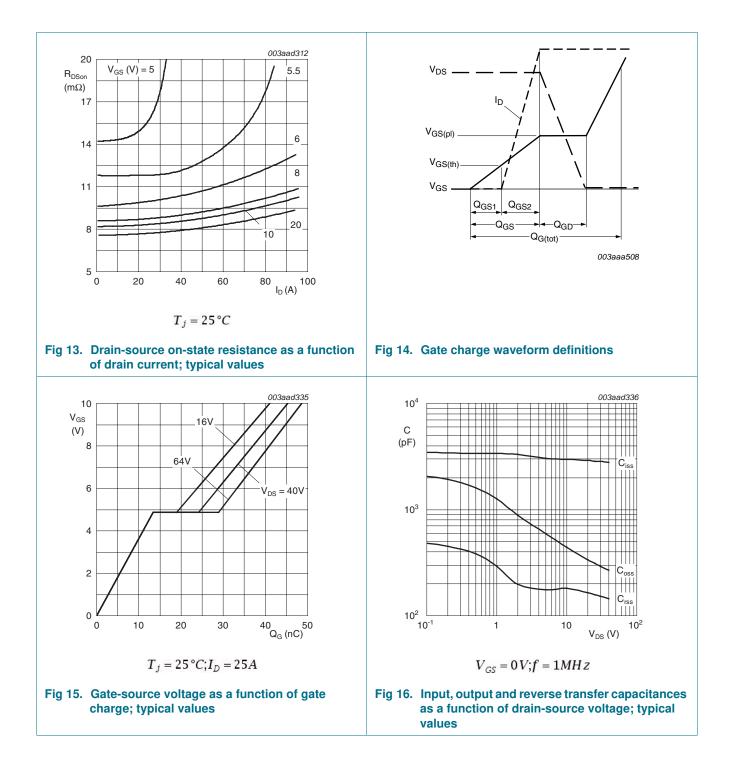
Parameter

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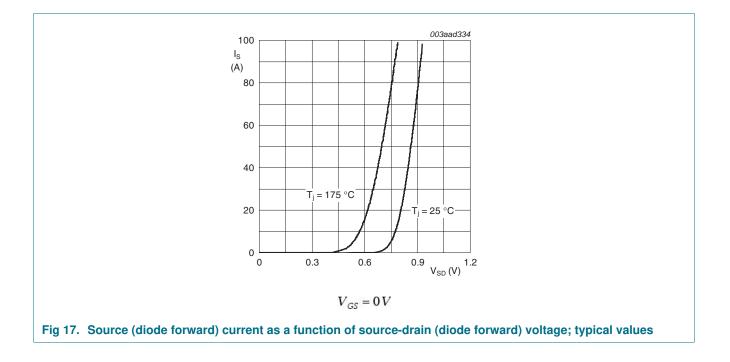
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7. Package outline

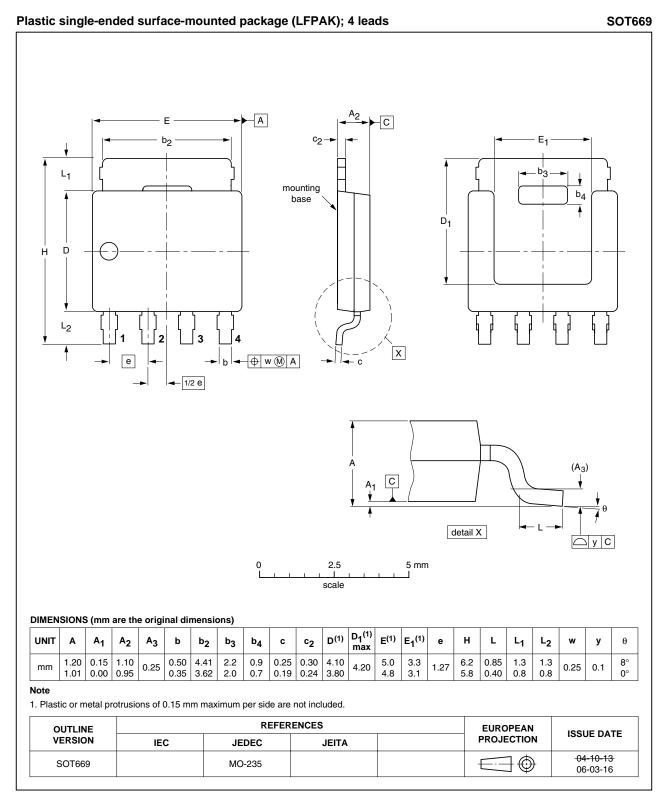


Fig 18. Package outline SOT669 (LFPAK)

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Product data sheet

8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-80YS v.2	20101028	Product data sheet	-	PSMN011-80YS v.1
Modifications:	Status changedVarious changed	d from objective to product. es to content.		
PSMN011-80YS v.1	20100226	Objective data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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